
2SB1058

Silicon PNP Epitaxial

HITACHI

Application

- Σ Low frequency power amplifier
- Σ Complementary pair with 2SD1489

Outline

TO-92 (1)



- 1. Emitter
- 2. Collector
- 3. Base

2SB1058

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-20	V
Collector to emitter voltage	V_{CEO}	-16	V
Emitter to base voltage	V_{EBO}	-6	V
Collector current	I_C	-2	A
Collector power dissipation	P_C	0.75	W
Junction temperature	T_J	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

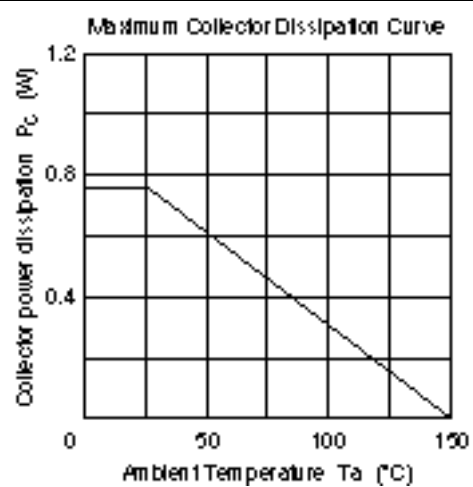
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-20	—	—	V	$I_C = -10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-16	—	—	V	$I_C = -1 \text{ mA}, R_{BE} = \bullet$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-6	—	—	V	$I_E = -10 \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-2	μA	$V_{CB} = -16 \text{ V}, I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	-0.2	μA	$V_{EB} = -6 \text{ V}, I_C = 0$
DC current transfer ratio	h_{FE}^{*1}	100	—	320		$V_{CE} = -2 \text{ V}, I_C = -0.1 \text{ A}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-0.3	V	$I_C = -1 \text{ A}, I_B = -0.1 \text{ A}$
Gain bandwidth product	f_T	—	80	—	MHz	$V_{CE} = -2 \text{ V}, I_C = -10 \text{ mA}$
Collector output capacitance	C_{ob}	—	50	—	pF	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$

Note: 1. The 2SB1058 is grouped by h_{FE} as follows.

B	C
100 to 200	160 to 320

See characteristic curves of 2SB738.



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